Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-8. (Canceled).

9. (Currently Amended) A method for producing semiconductor wafers from a semiconductor ingot, ~~wherein~~ wherein:

_____an oxygen concentration distribution in the growth axis direction is measured in the ingot state,

_____a position at which the oxygen concentration is maximum or ~~minimum~~ minimum, in a range of a predetermined length of the semiconductor ingot, is determined as a cut position according to the measurement results,

_____the ingot is cut in a perpendicular direction to the growth axis at the cut position into blocks each having the oxygen ~~concentrations~~ concentration being maximum at one end thereof and the oxygen concentration being minimum at the other end thereof~~and minimum at both ends thereof~~,

_____each of the blocks is sliced, and

_____thereby semiconductor wafers are produced.

10. (Currently Amended) The method for producing semiconductor wafers according to Claim 9, ~~wherein~~ wherein:

_____in the determination of ~~a cut~~the cut position, the semiconductor ingot is divided into blocks within a range of a preliminarily set length, ~~a position~~the position to be cut is adjusted so that the oxygen concentrations of each of the blocks are maximum at one end and minimum at the other end~~at both ends of each of the blocks are maximum and minimum~~, and when it is confirmed that the oxygen concentrations ~~at both ends of each of all~~

~~the blocks are maximum and minimum~~of each of all the blocks are maximum at one end and minimum at the other end, the position is determined as the cut position.

11. (Currently Amended) The method for producing semiconductor wafers according to Claim 9, ~~wherein~~ wherein:

_____in the determination of a cut position, the cut position is determined so that the oxygen concentrations are in a standard range and ~~maximum and minimum at both ends of each of the blocks~~maximum at one end and minimum at the other end of each of the blocks.

12. (Currently Amended) The method for producing semiconductor wafers according to Claim 9, ~~wherein~~ wherein:

_____samples are sliced from both ends of each of the blocks obtained by cutting the semiconductor ingot,

_____oxygen concentration in a plane of each of the samples is measured, and

_____if the oxygen concentration in a plane is in a standard range, the block is sliced, and thereby semiconductor wafers are produced.

13. (Currently Amended) The method for producing semiconductor wafers according to Claim 10, wherein:~~wherein~~

_____samples are sliced from both ends of each of the blocks obtained by cutting the semiconductor ingot,

_____oxygen concentration in a plane of each of the samples is measured, and

_____if the oxygen concentration in a plane is in a standard range, the block is sliced, and thereby semiconductor wafers are produced.

14. (Currently Amended) The method for producing semiconductor wafers according to Claim 11, wherein:~~wherein~~

_____samples are sliced from both ends of each of the blocks obtained by cutting the semiconductor ingot,

_____oxygen concentration in a plane of each of the samples is measured, and

_____if the oxygen concentration in a plane is in a standard range, the block is sliced, and thereby semiconductor wafers are produced.

15. (Currently Amended) The method for producing semiconductor wafers according to Claim 9, wherein:~~wherein~~

_____samples are sliced from both ends of each of the blocks obtained by cutting the semiconductor ingot,

_____oxygen concentration in a plane of each of the samples is measured, and

_____if the oxygen concentration in a plane is out of a standard range, another sample is further sliced from the end of the block and oxygen concentration in its plane is measured repeatedly, and then if the oxygen concentration in its plane becomes in the standard range, the block is sliced, and thereby semiconductor wafers are produced.

16. (Currently Amended) The method for producing semiconductor wafers according to Claim 10, wherein:~~wherein~~

_____samples are sliced from both ends of each of the blocks obtained by cutting the semiconductor ingot,

_____oxygen concentration in a plane of each of the samples is measured, and

_____if the oxygen concentration in a plane is out of a standard range, another sample is further sliced from the end of the block and oxygen concentration in its plane is measured repeatedly, and then if the oxygen concentration in its plane becomes in the standard range, the block is sliced, and thereby semiconductor wafers are produced.

17. (Currently Amended) The method for producing semiconductor wafers according to Claim 11, wherein:~~wherein~~

_____samples are sliced from both ends of each of the blocks obtained by cutting the semiconductor ingot,

_____oxygen concentration in a plane of each of the samples is measured, and _____if the oxygen concentration in a plane is out of a standard range, another sample is further sliced from the end of the block and oxygen concentration in its plane is measured repeatedly, and then if the oxygen concentration in its plane becomes in the standard range, the block is sliced, and thereby semiconductor wafers are produced.

18 (Previously Presented) The method for producing semiconductor wafers according to Claim 9, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

19. (Previously Presented) The method for producing semiconductor wafers according to Claim 10, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

20. (Previously Presented) The method for producing semiconductor wafers according to Claim 11, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

21. (Previously Presented) The method for producing semiconductor wafers according to Claim 12, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

22. (Previously Presented) The method for producing semiconductor wafers according to Claim 13, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

23. (Previously Presented) he method for producing semiconductor wafers according to Claim 14, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

24. (Previously Presented) The method for producing semiconductor wafers according to Claim 15, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

25. (Previously Presented) The method for producing semiconductor wafers according to Claim 16, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

26. (Previously Presented) The method for producing semiconductor wafers according to Claim 17, wherein as the semiconductor ingot, a silicon single crystal ingot having a diameter 150 mm or more is used.

27-28. (Canceled)